

A SINGLE RIE PROCESS FOR MIMCAP TOP AND BOTTOM PLATES

ABSTRACT

5 A method of forming MIM capacitor top (16) and
bottom (12) plates, using a first and second resist
(18/20) and a single RIE process. A first conductive
layer (12) is deposited over a substrate (10). An
insulating layer (14) is deposited over the first
10 conductive layer (12). A second conductive layer (16) is
deposited over the insulating layer (14). A first resist
(18) is deposited over the second conductive layer (16),
and the first resist (18) is patterned. A second resist
(20) is deposited over the first resist (18) and
15 patterned. The first and second resist (18/20) patterns
are simultaneously transferred to the first and second
conductive layers (12) and (16), respectively, by
exposure to a single reactive ion etch (RIE) process.